

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	4.0	OverallWafer Secondary Flat	90°CW (clockwise) from primary flat	Wafer Vendor
	5.0	Secondary Flat Length	18.00 +/- 2.00 mm	Wafer Vendor
	6.0	Overall Thickness	352.00 +/- 26.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<80.00µm	ADE 100%, SEMI MF1530
	9.0	Warp	<80.00µm	ADE 100%, SEMI MF1530
	10.0	Edge Chips	none	Bright Light, 100%
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	350.00 +/- 25.00 µm	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorus	Wafer Vendor
	17.0	Handle Resistivity	1~100 Ohm-cm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide and laser mark	Guaranteed by process
	BuriedOxide	19.0	Oxide Type	Thermal
20.0		Oxide Thickness	4,000.00 +/- 200.00 A	Nanospec centre point, 4%
21.0		Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	2.00 +/- 0.50 µm	Filmetrics, 100% 9-Pt (note3)
	24.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	25.0	Device Doping Type	N	Wafer Vendor
	26.0	Device Dopant	Phosphorus	Wafer Vendor
	27.0	Device Growth Method	CZ	Wafer Vendor
	28.0	Device Resistivity	3~5 Ohm-cm	Wafer Vendor
	29.0	Voids	None	Bright Light, 100% (note 2)
	30.0	Scratches	Frontside - no scratches allowed. Backside - light handling marks	Bright Light, 100% (note 2)
	31.0	Haze	None	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information